

# Quad 2-Input NAND Schmitt Trigger

The MC74VHCT132A is an advanced high speed CMOS Schmitt NAND trigger fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

Pin configuration and function are the same as the MC74VHC00, but the inputs have hysteresis and, with its Schmitt trigger function, the VHCT132A can be used as a line receiver which will receive slow input signals.

The VHCT inputs are compatible with TTL levels. This device can be used as a level converter for interfacing 3.3V to 5.0V, because it has full 5V CMOS level output swings.

The VHCT132A input structures provide protection when voltages between 0V and 5.5V are applied, regardless of the supply voltage. The output structures also provide protection when  $V_{CC}=0V$ . These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7V, allowing the interface of 5V systems to 3V systems.

- High Speed:  $t_{PD} = 4.9$ ns (Typ) at  $V_{CC} = 5V$
- Low Power Dissipation:  $I_{CC} = 2\mu A$  (Max) at  $T_A = 25$ °C
- TTL-Compatible Inputs:  $V_{IL} = 0.8V$ ;  $V_{IH} = 2.0V$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2V to 5.5V Operating Range
- Low Noise:  $V_{OLP} = 0.8V$  (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA
- ESD Performance: HBM > 2000V; Machine Model > 200V
- Chip Complexity: 72 FETs or 18 Equivalent Gates

# MC74VHCT132A



**D SUFFIX** 14-LEAD SOIC PACKAGE CASE 751A-03



**DT SUFFIX** 14-LEAD TSSOP PACKAGE CASE 948G-01



M SUFFIX 14-LEAD SOIC EIAJ PACKAGE CASE 965-01

#### ORDERING INFORMATION

MC74VHCTXXAD SOIC
MC74VHCTXXADT TSSOP
MC74VHCTXXAM SOIC EIAJ

#### **FUNCTION TABLE**

Inp	Output	
Α	Y	
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

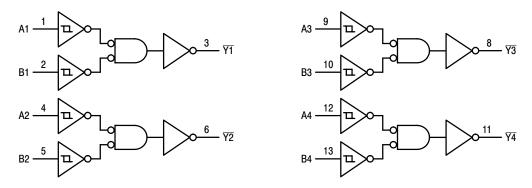


Figure 1. Logic Diagram

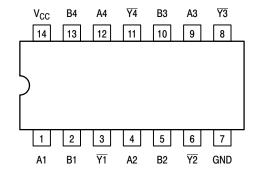


Figure 2. Pinout: 14-Lead Packages (Top View)

#### **MAXIMUM RATINGS\***

Symbol	Parameter	Parameter			
V <sub>CC</sub>	DC Supply Voltage	- 0.5 to + 7.0	V		
V <sub>in</sub>	DC Input Voltage	- 0.5 to + 7.0	V		
V <sub>out</sub>	DC Output Voltage	$-0.5$ to $V_{CC} + 0.5$	V		
I <sub>IK</sub>	Input Diode Current	- 20	mA		
I <sub>OK</sub>	Output Diode Current		± 20	mA	
l <sub>out</sub>	DC Output Current, per Pin		± 25	mA	
Icc	DC Supply Current, V <sub>CC</sub> and GN	D Pins	± 50	mA	
P <sub>D</sub>	Power Dissipation in Still Air,	SOIC Packages† TSSOP Package†	500 450	mW	
T <sub>stg</sub>	Storage Temperature		- 65 to + 150	°C	

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

†Derating — SOIC Packages: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage	4.5	5.5	V
V <sub>in</sub>	DC Input Voltage	0	5.5	V
V <sub>out</sub>	DC Output Voltage	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types	- 40	+ 85	°C

#### DC ELECTRICAL CHARACTERISTICS

			Vcc	٦	Γ <sub>A</sub> = 25°0	A = 25°C T <sub>A</sub> ≤		$T_A \le 85^{\circ}C$ $T_A$		≤ 125°C	
Symbol	Parameter	Test Conditions	V	Min	Тур	Max	Min	Max	Min	Max	Unit
V <sub>T+</sub>	Positive Threshold Voltage		3.0 4.5 5.5			1.7 2.0 2.0		1.6 2.0 2.0		1.6 2.0 2.0	V
V <sub>T</sub> –	Negative Threshold Voltage		3.0 4.5 6.0	0.35 0.5 0.6			0.35 0.5 0.6		0.35 0.5 0.6		V
V <sub>H</sub>	Hysteresis Voltage		3.0 4.5 5.5	0.30 0.40 0.50		1.20 1.40 1.60	0.30 0.40 0.50	1.20 1.40 1.60	0.30 0.40 0.50	1.20 1.40 1.60	V
V <sub>OH</sub>	Minimum High–Level Output Voltage I <sub>OH</sub> = –50μA	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		I <sub>OH</sub> = - 4mA I <sub>OH</sub> = - 8mA	4.5 5.5	2.58 3.94			2.48 3.80		2.34 3.66		
V <sub>OL</sub>	Maximum Low–Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		$I_{OL} = 4mA$ $I_{OL} = 8mA$	4.5 5.5			0.36 0.36		0.44 0.44		0.52 0.52	
I <sub>IN</sub>	Maximum Input Leakage Current	V <sub>IN</sub> = 5.5V or GND	0 to 5.5			± 0.1		± 1.0		± 1.0	μА
I <sub>CC</sub>	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			2.0		20		40	μА
Ісст	Quiescent Supply Current	Input: V <sub>IN</sub> = 3.4V	5.5			1.35		1.50		1.65	mA
I <sub>OPD</sub>	Output Leakage Current	V <sub>OUT</sub> = 5.5V	0.0			0.5		5.0		10	μΑ

<sup>\*</sup> Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute—maximum—rated conditions is not implied.

## AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns)

			7	T <sub>A</sub> = 25°C		T <sub>A</sub> = -		<b>T</b> <sub>A</sub> ≤ 1	125°C	
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, A or B to $\overline{Y}$	$V_{CC} = 3.3 \pm 0.3 \text{ V C}_{L} = 15 \text{pF}$ $C_{L} = 50 \text{pF}$		7.6 10.1	11.9 15.4	1.0 1.0	14.0 17.5		16.5 20.0	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V C}_{L} = 15 \text{pF}$ $C_{L} = 50 \text{pF}$		4.9 6.4	7.7 9.7	1.0 1.0	9.0 11.0		11.0 13.0	
C <sub>in</sub>	Maximum Input Capacitance			4	10		10		10	pF

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
$C_{PD}$	Power Dissipation Capacitance (Note 1.)	16	pF

C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>/4 (per gate). C<sub>PD</sub> is used to determine the no–load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

## NOISE CHARACTERISTICS (Input $t_{r} = t_{f} = 3.0 \text{ns}, C_{L} = 50 \text{pF}, V_{CC} = 5.0 \text{ V})$

		T <sub>A</sub> = 25°C		
Symbol	Characteristic	Тур	Max	Unit
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.3	0.8	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	- 0.3	- 0.8	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		3.5	V
$V_{ILD}$	Maximum Low Level Dynamic Input Voltage		1.5	V

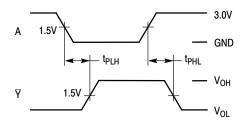
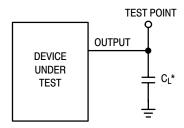


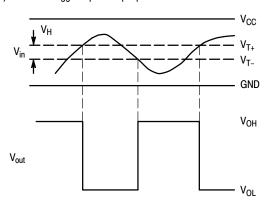
Figure 3. Switching Waveforms



\*Includes all probe and jig capacitance

Figure 4. Test Circuit

## (a) A Schmitt-Trigger Squares Up Inputs With Slow Rise and Fall Times



#### (b) A Schmitt-Trigger Offers Maximum Noise Immunity

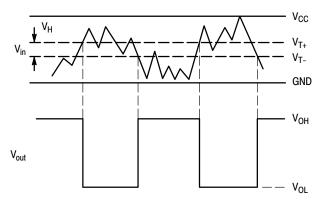
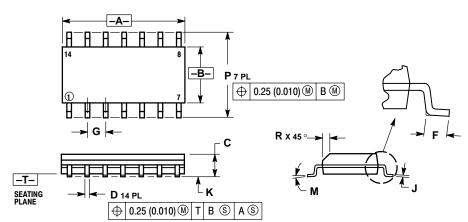


Figure 5. Typical Schmitt-Trigger Applications

#### **OUTLINE DIMENSIONS**

**D SUFFIX** SOIC-14 CASE 751A-03 **ISSUE F** 

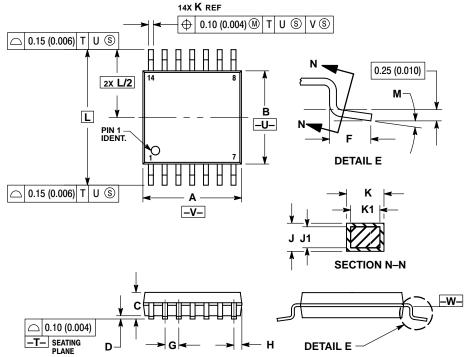


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
  4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
  5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7°	0 °	7°
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

#### **OUTLINE DIMENSIONS**

#### **DT SUFFIX TSSOP** CASE 948G-01 **ISSUE 0**

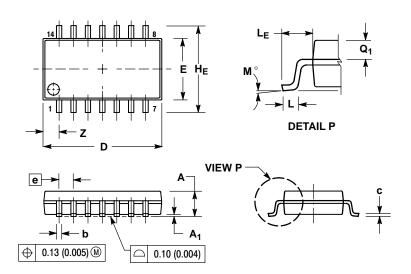


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
- DIMENSIONING AND TOLERANDING PER ANSI Y14.5M, 1982.
   CONTROLLING DIMENSION: MILLIMETER.
   DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15
- OR GATE BURRS SHALL NOT EXCEED 0.15
  (0.006) PER SIDE.
  4. DIMENSION B DOES NOT INCLUDE INTERLEAD
  FLASH OR PROTRUSION. INTERLEAD FLASH OR
  PROTRUSION SHALL NOT EXCEED
  0.25 (0.010) PER SIDE.
  5. DIMENSION K DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR
  PROTRUSION SHALL BE 0.08 (0.03) TOTAL IN
  EXCESS OF THE K DIMENSION AT MAXIMUM
  MATERIAL CONDITION.
  6. TERMINAL NUMBERS ARE SHOWN FOR
  REFERENCE ONLY.
  7. DIMENSION A AND B ARE TO BE DETERMINED
  AT DATUM PLANE-W-

	MILLIN	IETERS	INCHES			
DIM	MIN	MAX	MIN	MAX		
Α	4.90	5.10	0.193	0.200		
В	4.30	4.50	0.169	0.177		
С		1.20		0.047		
D	0.05	0.15	0.002	0.006		
F	0.50	0.75	0.020	0.030		
G	0.65 BSC		0.026	BSC		
Н	0.50	0.60	0.020	0.024		
J	0.09	0.20	0.004	0.008		
J1	0.09	0.16	0.004	0.006		
K	0.19	0.30	0.007	0.012		
K1	0.19	0.25	0.007	0.010		
L	6.40		0.252 BSC			
M	0°	8°	0°	8°		

#### **OUTLINE DIMENSIONS**

**M SUFFIX** SO-14 **CASE 965-01 ISSUE 0** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTR
- PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006)
  PER SIDE.

  1 TERMINAL NUMBERS ARE SHOWN FOR
  REFERENCE ONLY.

  5. THE LEAD WIDTH DIMENSION (b) DOES NOT
  INCLUDE DAMBAR PROTRUSION. ALLOWABLE
  DAMBAR PROTRUSION SHALL BE 0.08 (0.003)
  TOTAL IN EXCESS OF THE LEAD WIDTH
  DIMENSION AT MAXIMUM MATERIAL CONDITION.
  DAMBAR CANNOT BE LOCATED ON THE LOWER
  RADIUS OR THE FOOT. MINIMUM SPACE
  BETWEEN PROTRUSIONS AND ADJACENT LEAD
  TO BE 0.46 (0.018). TO BE 0.46 ( 0.018).

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050	BSC
HE	7.40	8.20	0.291	0.323
0.50	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10 °
$Q_1$	0.70	0.90	0.028	0.035
Z		1.42		0.056

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